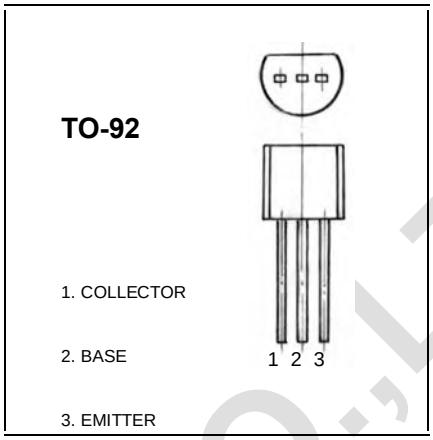
BC546, B
BC547, A, B, C
BC548, A, B, C

TRANSISTOR (NPN)



FEATURES

Power dissipation

P_{CM}: 0.625 W (Tamb=25℃)

Collector current

I_{CM}: 0.1 A

Collector-base voltage

V_{CBO}: BC546 80 V
BC547 50 V
BC548 30 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter		Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	BC546	V_{CBO}	Ic= 100μA , I_E=0	80		V
	BC547			50		
	BC548			30		
Collector-emitter breakdown voltage	BC546	V_{CEO}	I_C= 1mA , I_B=0	65		V
	BC547			45		
	BC548			30		
Emitter-base breakdown voltage		V_{EBO}	I_E= 10μA, I_C=0	6		V
Collector cut-off current	BC546	I_{CBO}	V_{CB}= 70V, I_E=0		0.1	μA
	BC547		V_{CB}= 50 V, I_E=0			
	BC548		V_{CB}= 30V, I_E=0			
Collector cut-off current	BC546	I_{CEO}	V_{CE}= 60 V, I_B=0		0.1	μA
	BC547		V_{CE}= 45 V, I_B=0			
	BC548		V_{CE}= 30 V, I_B=0			
Emitter cut-off current	BC546	I_{EBO}	V_{EB}= 5V, I_C=0		0.1	μA
	BC547					
	BC548					
DC current gain	BC546	$h_{FE(1)}$	V_{CE}=5V, I_C= 2mA	110	450	
	BC547			110	800	
	BC548			110	800	
	BC547A/548A			110	220	
	BC546B/BC547B/BC548B			200	450	
	BC546C/BC547C/BC548C			420	800	
Collector-emitter saturation voltage		$V_{CE(sat)}$	I_C=100 mA, I_B= 5mA		0.3	V
Base-emitter saturation voltage		$V_{BE(sat)}$	I_C= 100 mA, I_B=5mA		1	V
Transition frequency		f_T	V_{CE}= 5V, I_C= 10mA f = 100MHz	150		MHz